

# Design of a 72-Channel, 40 Gbps PAM3 ATE-on-Bench Test System for GDDR7 Memories

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# The GDDR7 Specification

## **A major step forward...**

- 1 Tbps throughput on a single memory device
- 64 Gbit of storage on a single memory device



# The GDDR7 Specification

## **A major step forward...**

- 1 Tbps throughput on a single memory device
- 64 Gbit of storage on a single memory device

## **An unprecedented testing challenge...**

- How to perform BERT-based I/O characterization
- How to perform memory cell testing



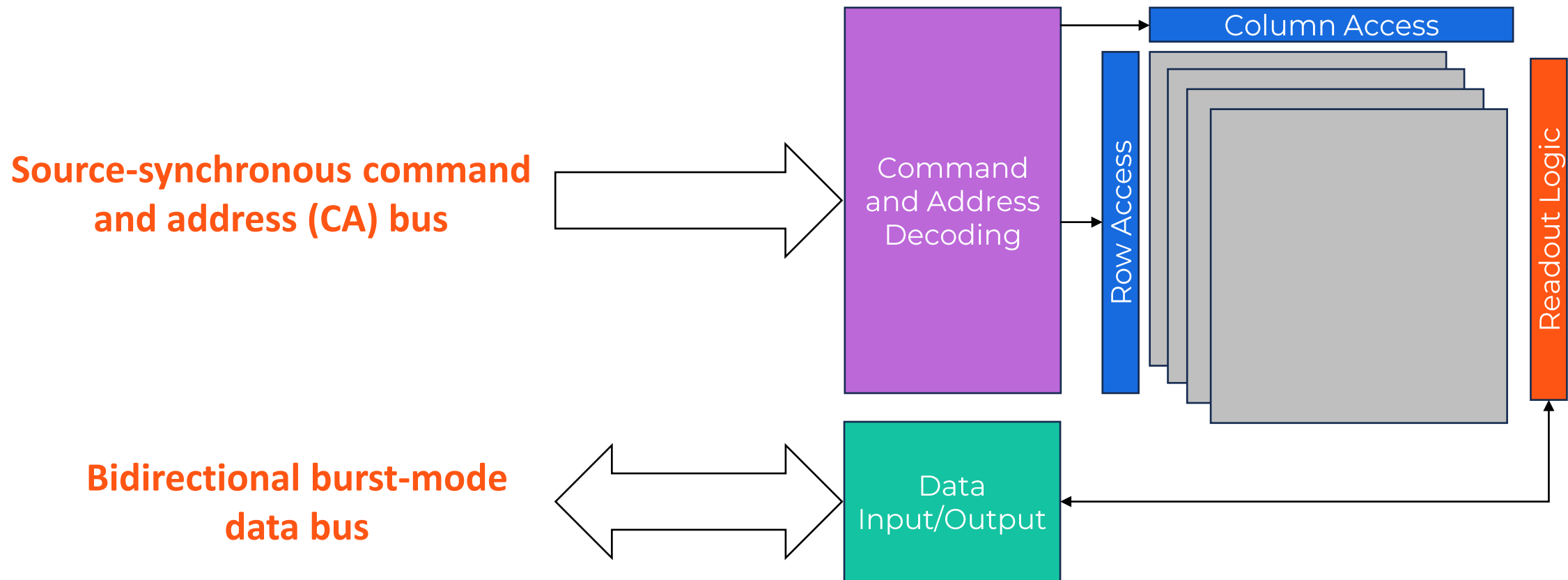
# Focus of This Presentation

## Design of an ATE on Bench Solution for GDDR7



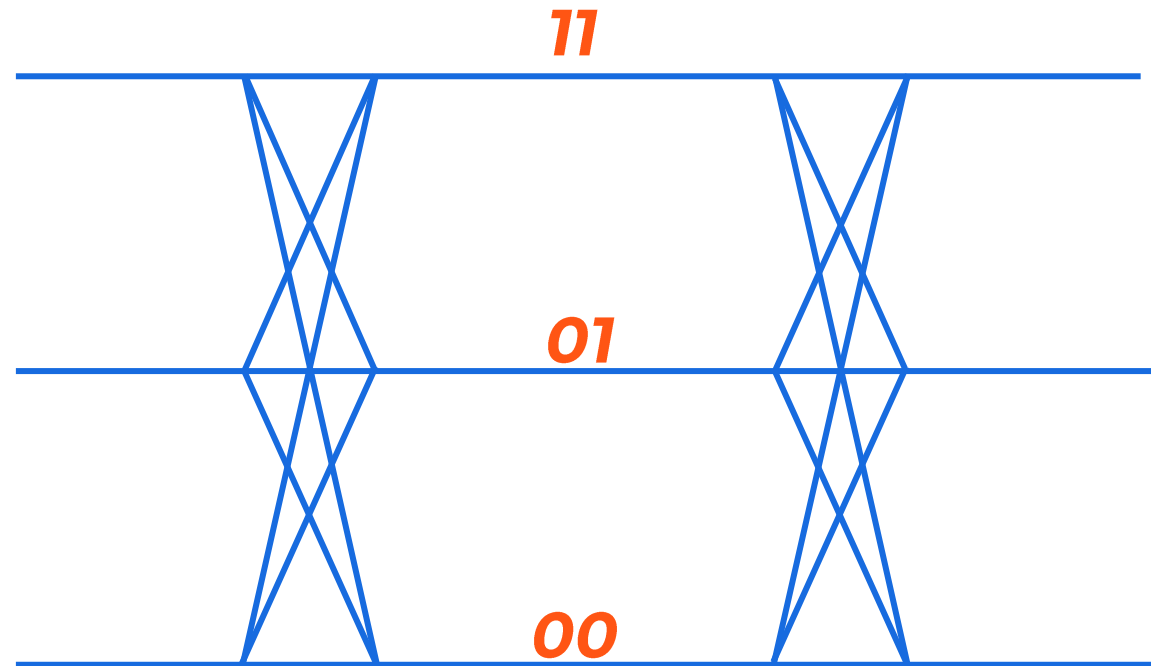
# Overview of the GDDR7 Specification

It still looks like a DDR memory interface



# Overview of the GDDR7 Specification

It introduces **PAM3** signaling



# GDDR7 Is Unlike Other PAM3 or PAM4 Standards

High-Speed

Single-Ended

- Ethernet, USB, or PCIe are all high-speed, but they rely on differential signaling
- The GDDR7 DQ pins are all single-ended, and this requires more careful design



# GDDR7 Is Unlike Other PAM3 or PAM4 Standards

High-Speed

Single-Ended

Bidirectional

PAM3

- Ethernet, USB, or PCIe all have separate Tx and Rx lanes, so the PHY implementation does not require bidirectional I/Os
- The GDDR7 DQ pins are all bidirectional I/Os, and this is a major design challenge





# GDDR7 Is Unlike Other PAM3 or PAM4 Standards

High-Speed

Single-Ended

Bidirectional

PAM3

Burst-Mode

- Ethernet, USB, or PCIe all rely on CDR-based SerDes (with continuous data)
- The GDDR7 interface is burst-mode with very short burst sizes. So, it is not possible to use a CDR



# GDDR7 Is Unlike Other PAM3 or PAM4 Standards

High-Speed

Single-Ended

Bidirectional

PAM3

Burst-Mode

**GDDR7 poses significant electrical test and characterization challenges**



# Protocol-Level Lane to Lane Interactions

CA Bus Training

DQ Bus Training

- Drive CA and measure DQ
- Drive CA, DQ and measure DQ
- DQ has both write and read training



# Protocol-Level Lane to Lane Interactions

CA Bus Training

DQ Bus Training

PAM3 Encoders

- Three different PAM3 encoders (11b7s, 3b2s, 2b1s)
- PAM3 encoders are distributed across lanes



# Protocol-Level Lane to Lane Interactions

CA Bus Training

DQ Bus Training

PAM3 Encoders

Data Integrity

- CRC on read/write transfers
- ECC on read/write transfers and on-die memory cells
- Command address parity



# Protocol-Level Lane to Lane Interactions

CA Bus Training

DQ Bus Training

PAM3 Encoders

Data Integrity

**GDDR7 poses significant protocol test and characterization challenges**



# Design of the ATE on Bench Solution

**Parallel, Protocol-Aware BERT & Functional Memory Tester...**



# Goals of the Design

## PHY Level Testing and Characterization

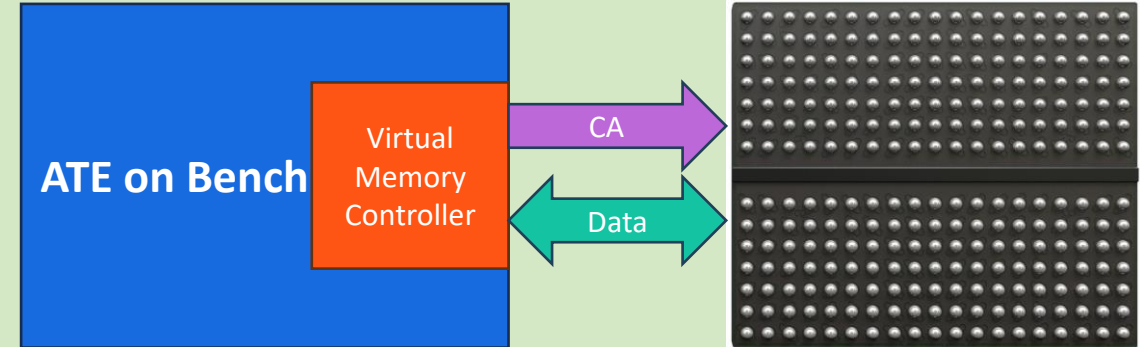
Adjustable voltage and timing parameters on all pins (including jitter injection)

Act as a high-performance, parallel, protocol-aware BERT

## Virtual Memory Controller

Act as a CPU/GPU memory controller

Protocol-compliant stimulus for all memory commands



## Functional Stress Testing

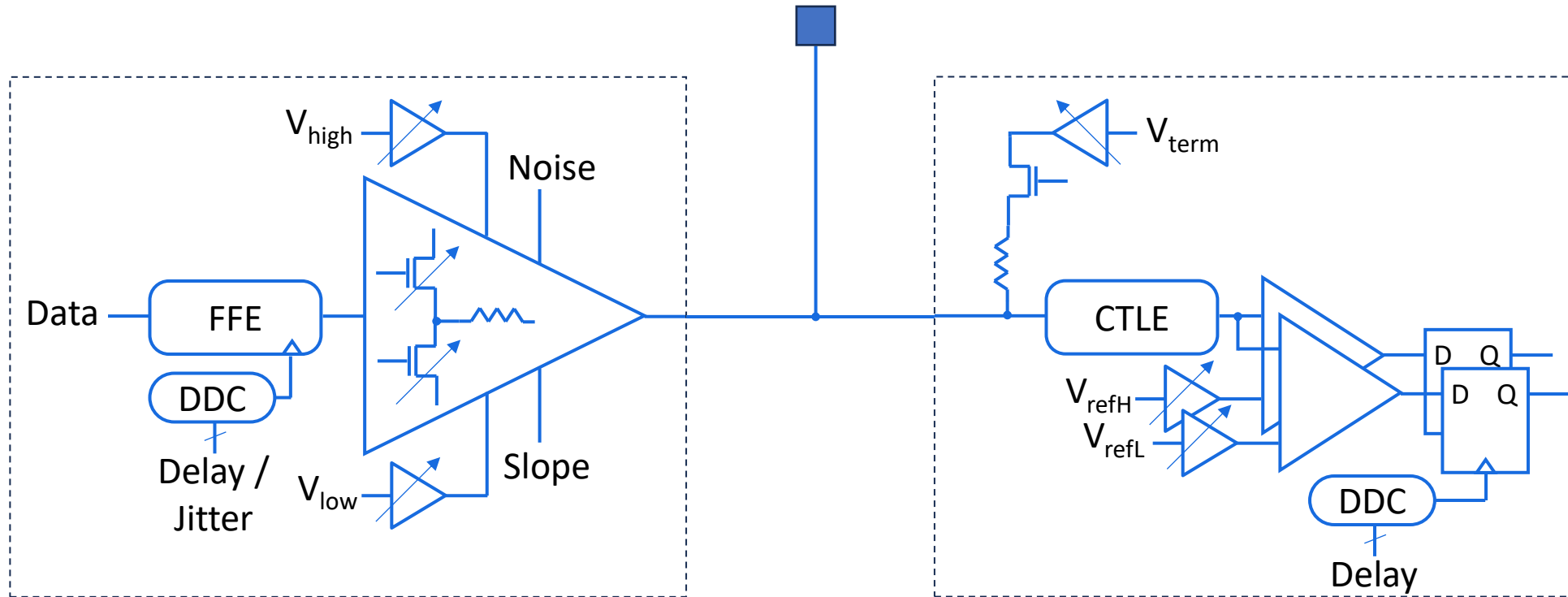
What are the limits of the device? Verify functional behavior while pushing command timings,

data rate and other parameters out of spec

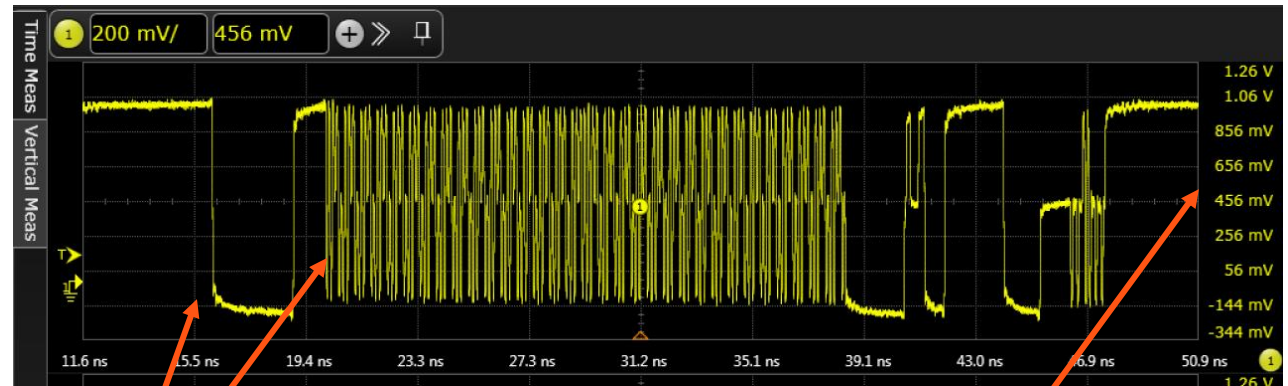
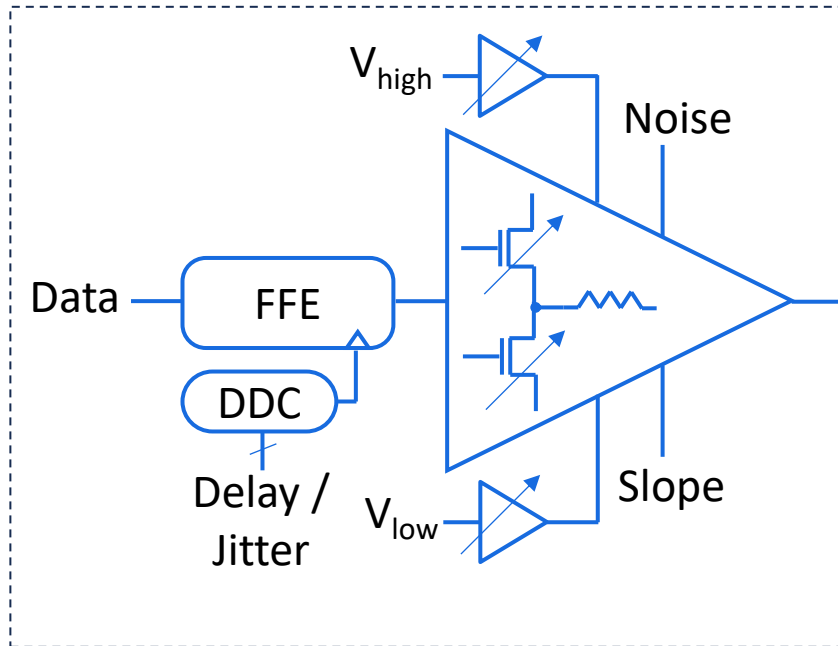




# Pin Electronic Design



# Pin Electronic Design – Cycle Level Control

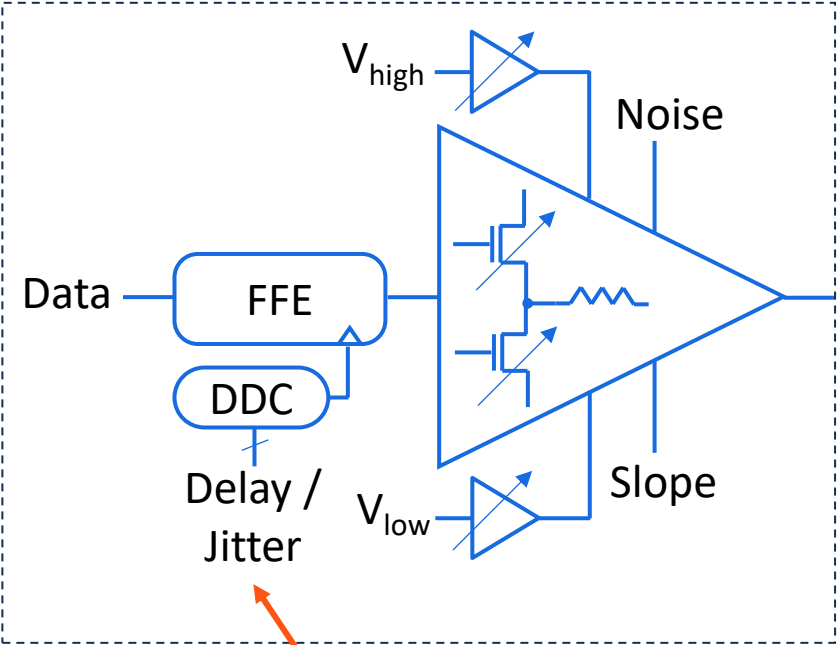


Arbitrarily switch between NRZ and PAM3 signaling

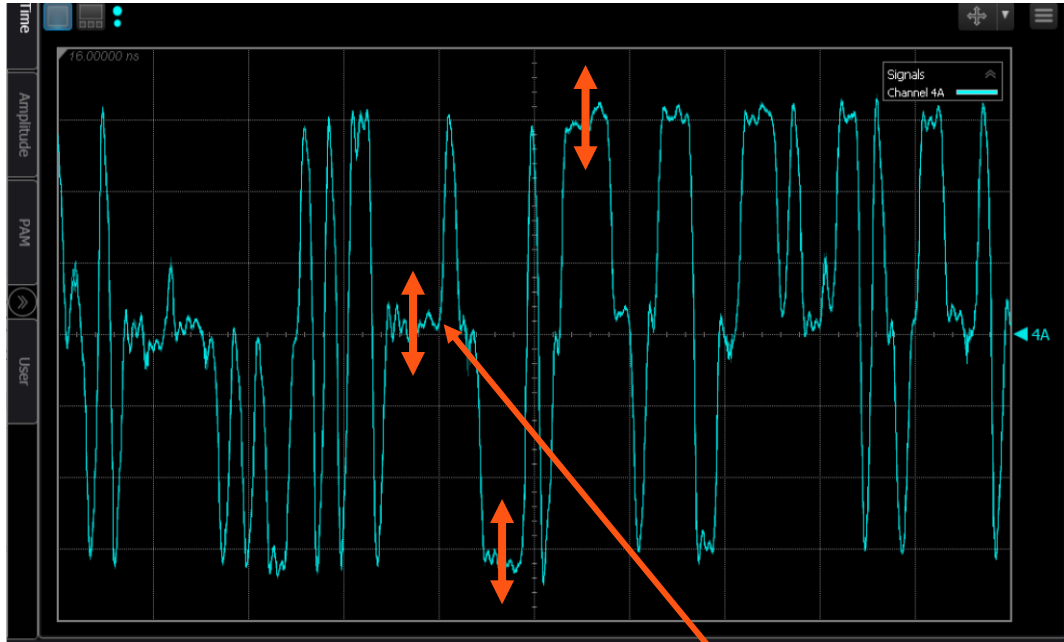
Wide voltage range



# Pin Electronic Design – Impairments



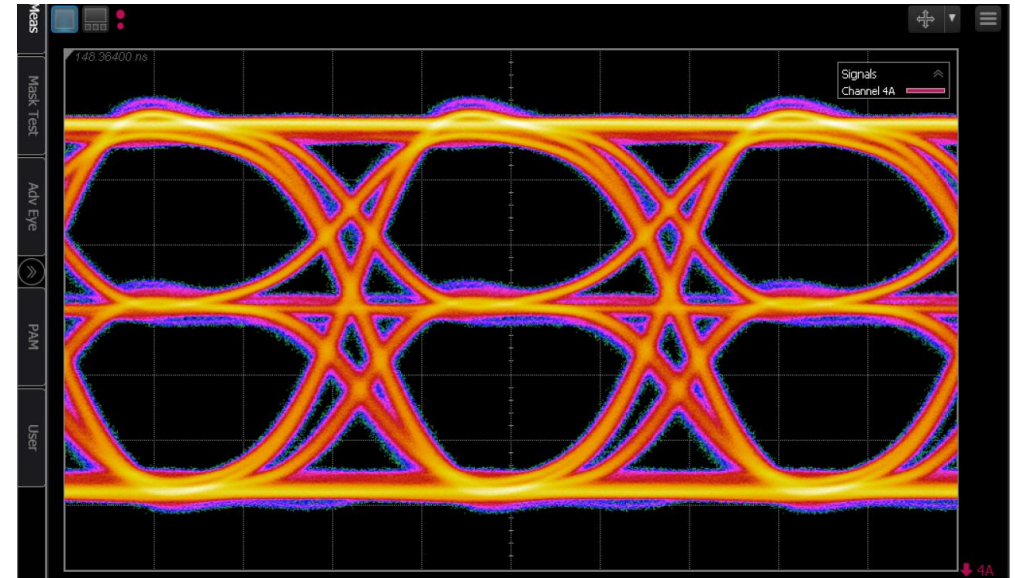
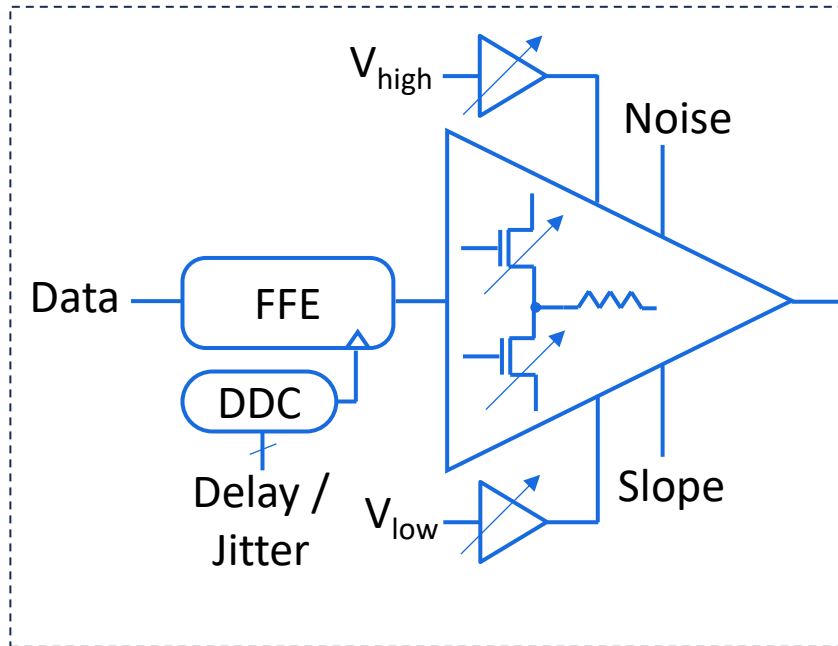
Digital to Delay Converter is used for programming both static skew and jitter



Individual control over low, mid, and high voltages



# Pin Electronic Design – Designed for 40 Gbps

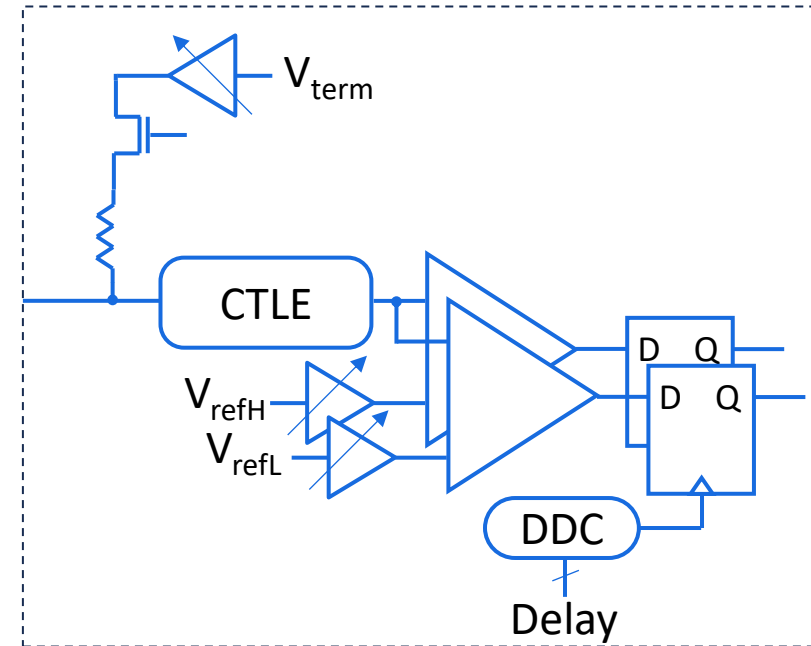
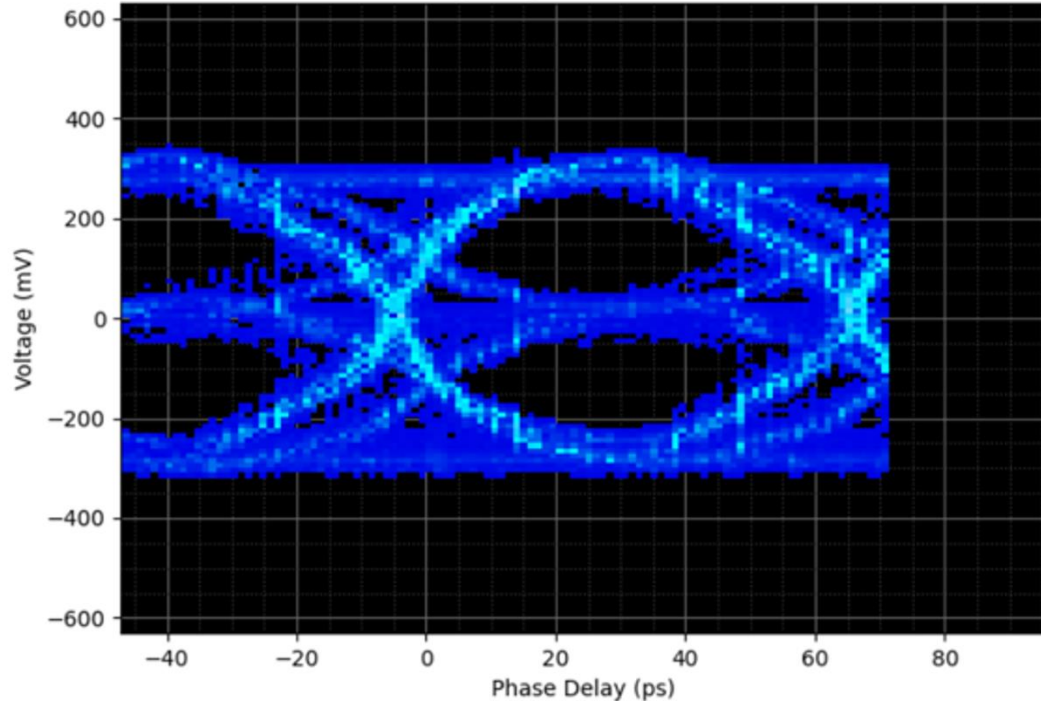


Superior signal integrity  
at 28 Gbps and beyond



# Pin Electronic Design – Shmoo Capability

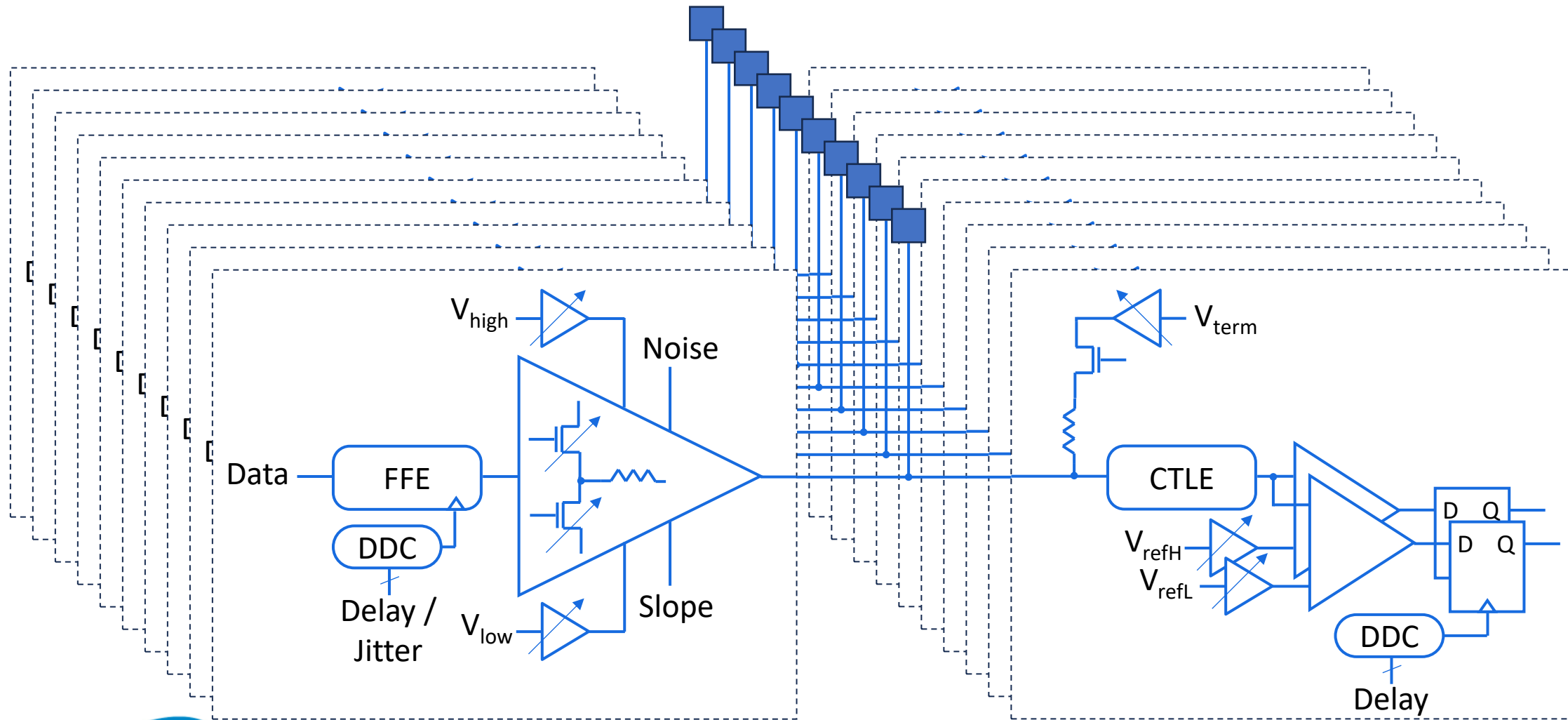
## DUT DQ Read at 28 Gbps



Receivers act as a window comparator to perform parallel PAM3 eye diagram measurement



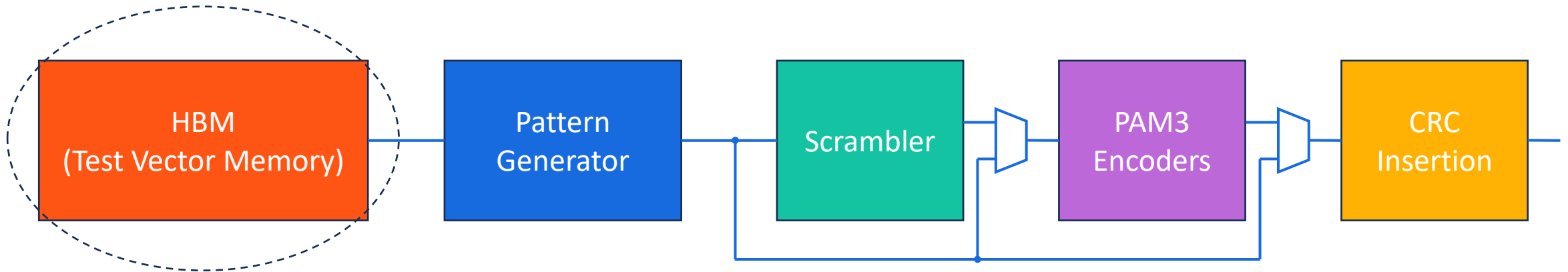
# All I/O Work as a Bus – 72 I/O per Package



Auto calibration guarantees phase matching on Tx & Rx



# Pattern Handling Architecture



- HBM memory is used behind all pins in order to sustain bandwidth
  - 2.88 Tbps of available test vector bandwidth
- Option for hardware-based or software-based scrambling, PAM3 encoding, and mapping
- Instruction sequencer includes “hold” and “idle” patterns

# Software Architecture

The screenshot shows a software configuration interface for DDR components. On the left is a sidebar with a tree view under the 'DDR' category, listing various controllers and parameters. The main area is divided into two panes: 'Components' and 'gddrController1'. The 'Components' pane shows a list of components including gddrChannelLabeling1, gddrController1 (highlighted), gddrParams1, gddrPhyParams1, and pam3Protocol. The 'gddrController1' pane displays a list of configuration parameters with their current values and dropdown menus for selection.

Parameter	Value
deviceSerialNum	1234
trainingDataFolderPath	
memBusesUnderTest	ABCD
phyParams	gddrPhyParams1
gddrParams	gddrParams1
rxChannelLabeling	gddrChannelLabeling1
txChannelLabeling	gddrChannelLabeling1
calibrateZq	True
trainingDataCaPhase	auto
caPhaseTrainingNumStepsPerUi	32
trainingDataCaVref	auto
caVrefTrainingStepSize	1
trainingDataReadVref	auto
trainingDataReadPam3EyeOffset	auto
trainingDataReadPhase	auto

BERT:  
Configure all impairments

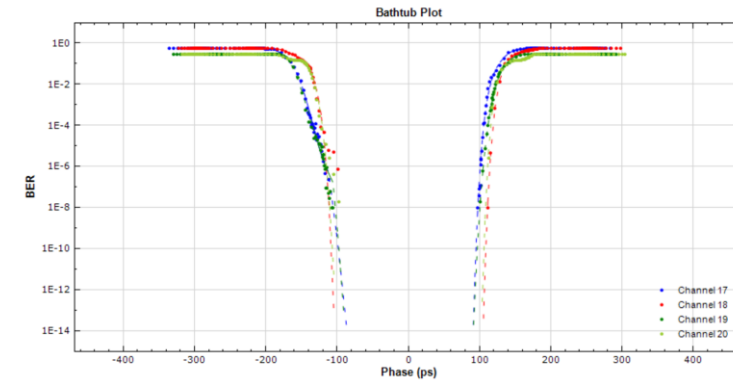
Virtual Memory Controller:  
automatically initialize and  
train the interfaces



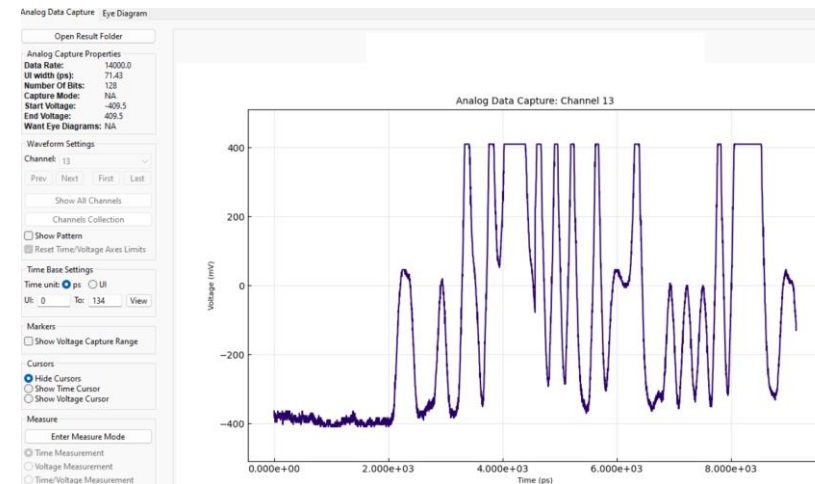


# PHY Characterization – Transmitter Interfaces

- Clock to data skew measurement
  - RCK to DQ
- BERT measurements on clock and data
  - Long duration error rate tests
  - Eye diagrams
  - Jitter measurements
  - Slew rate measurements



RCK and DQ jitter & skew measurement

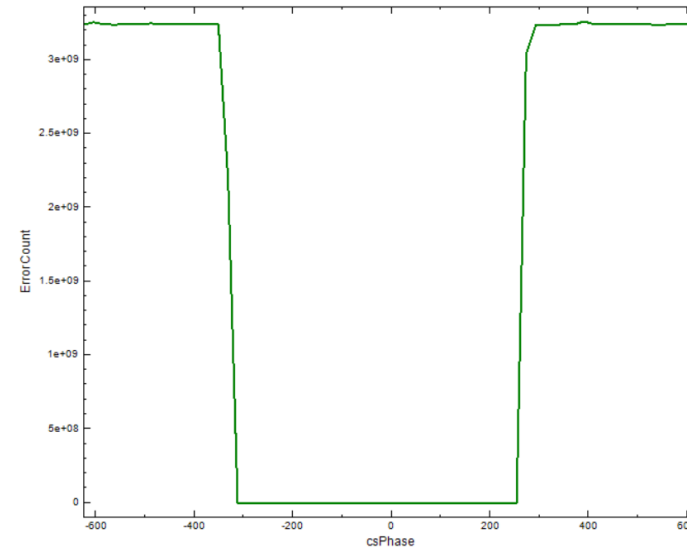
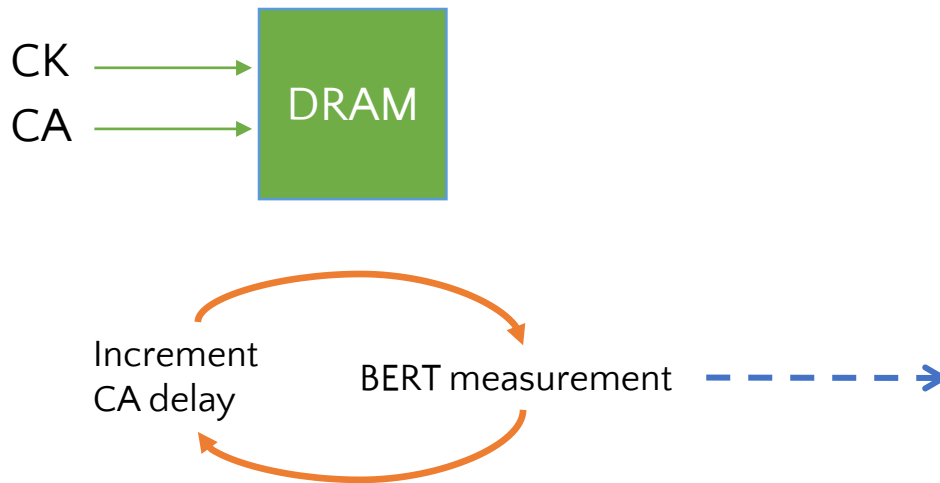


RCK and DQ waveform measurement

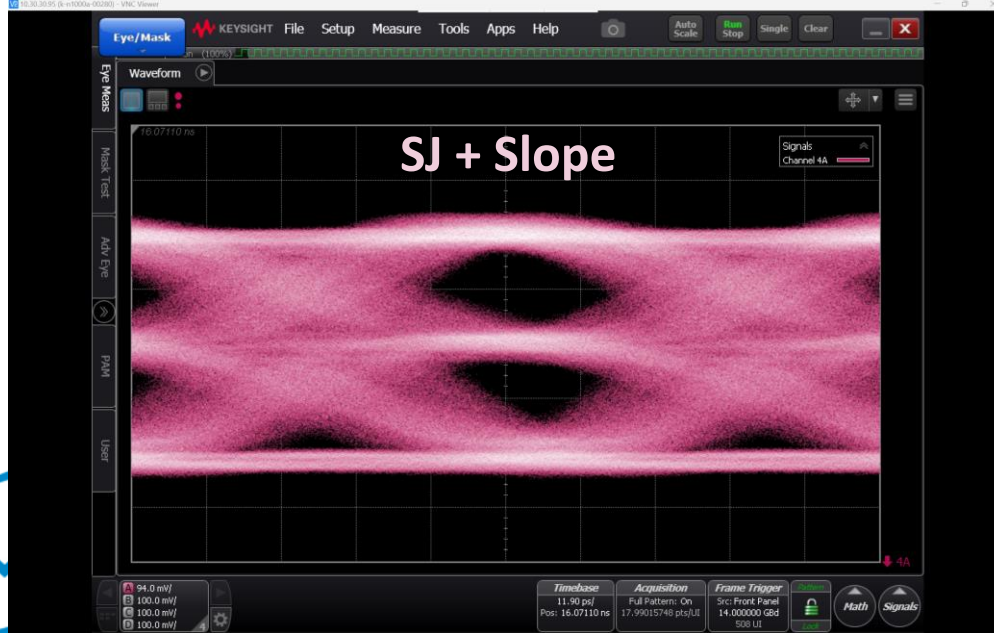
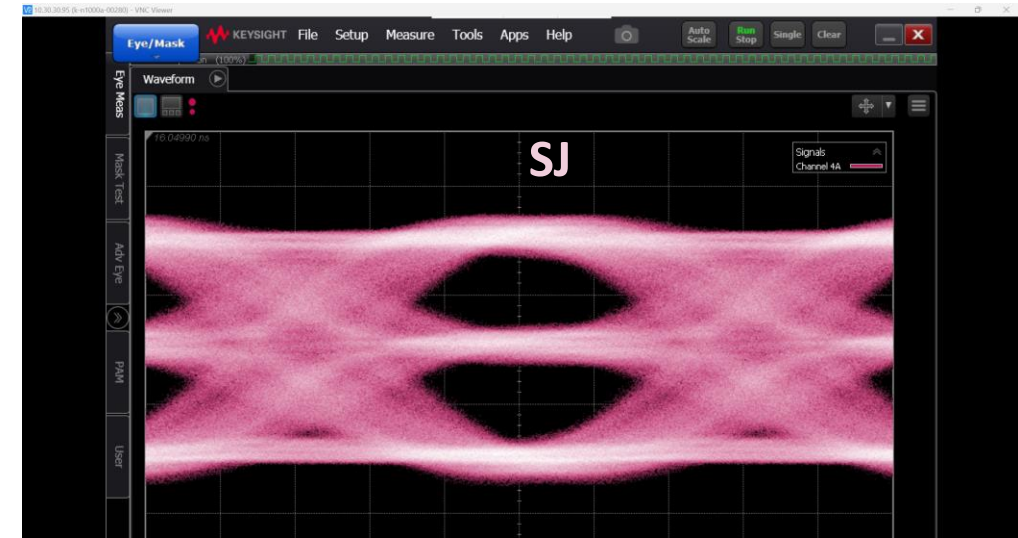
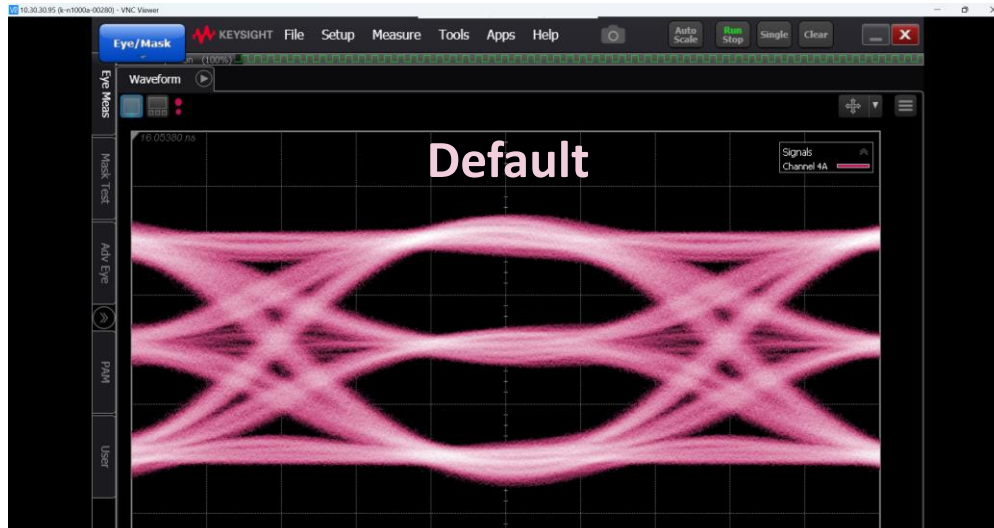


# PHY Characterization – Receiver Interfaces

- Measure horizontal and vertical eye opening at receiver while applying different stressors
  - Timing & jitter sensitivity – clock to data
  - Voltage sensitivity
  - Stressed eye

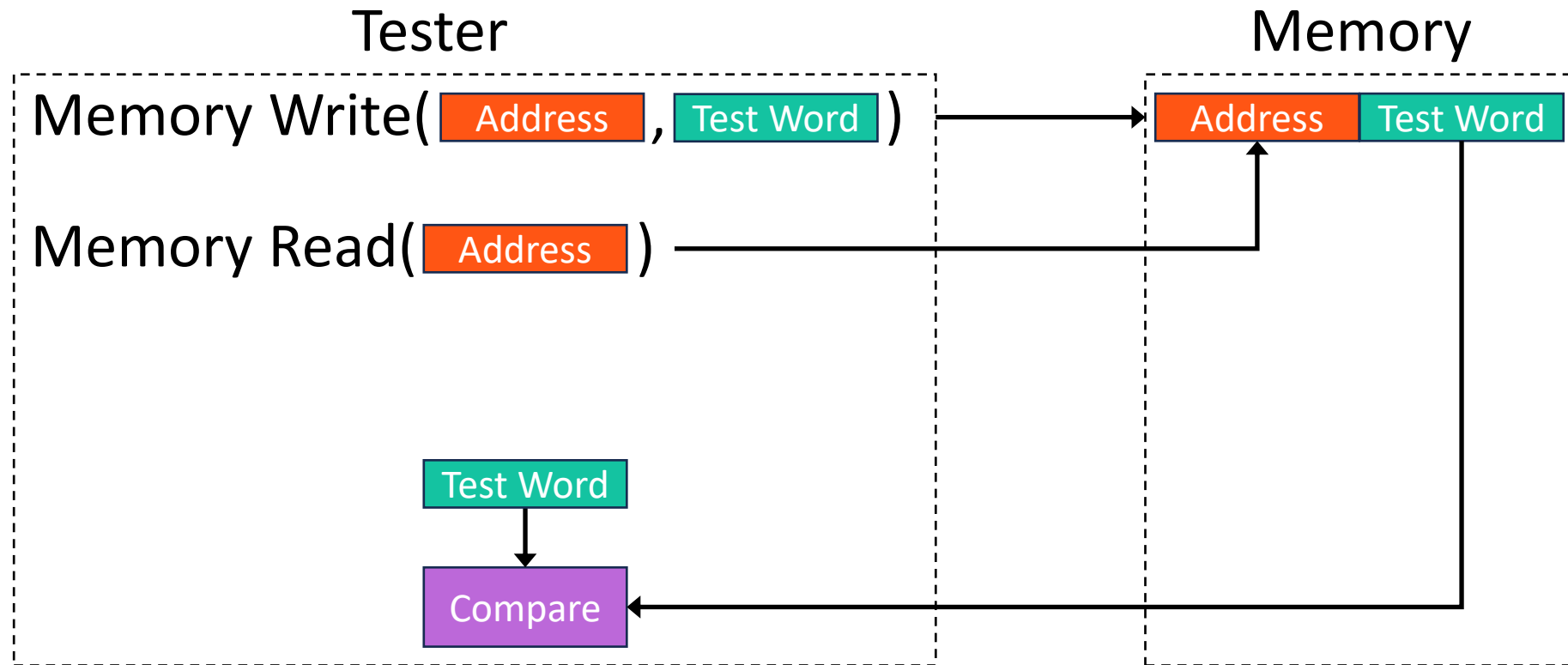


# Receiver Stressed Eye Generation



# Memory Stress Test Pattern Scheduling

- Write-read-compare at each memory location
- Data Pattern = User-configurable Test Word



# Summary

- The high-speed, burst-mode, single-ended, bidirectional, PAM3 signaling in GDDR7 all present significant electrical design and validation challenges
- The multiple training modes in GDDR7 also present design validation and stress testing challenges
- We have presented the design of an ATE on Bench solution for testing GDDR7 memories
  - Acts like a high-performance BERT for electrical characterization
  - Acts like a high-speed memory ATE for functional memory testing



# Thank You!



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<https://introspect.ca>

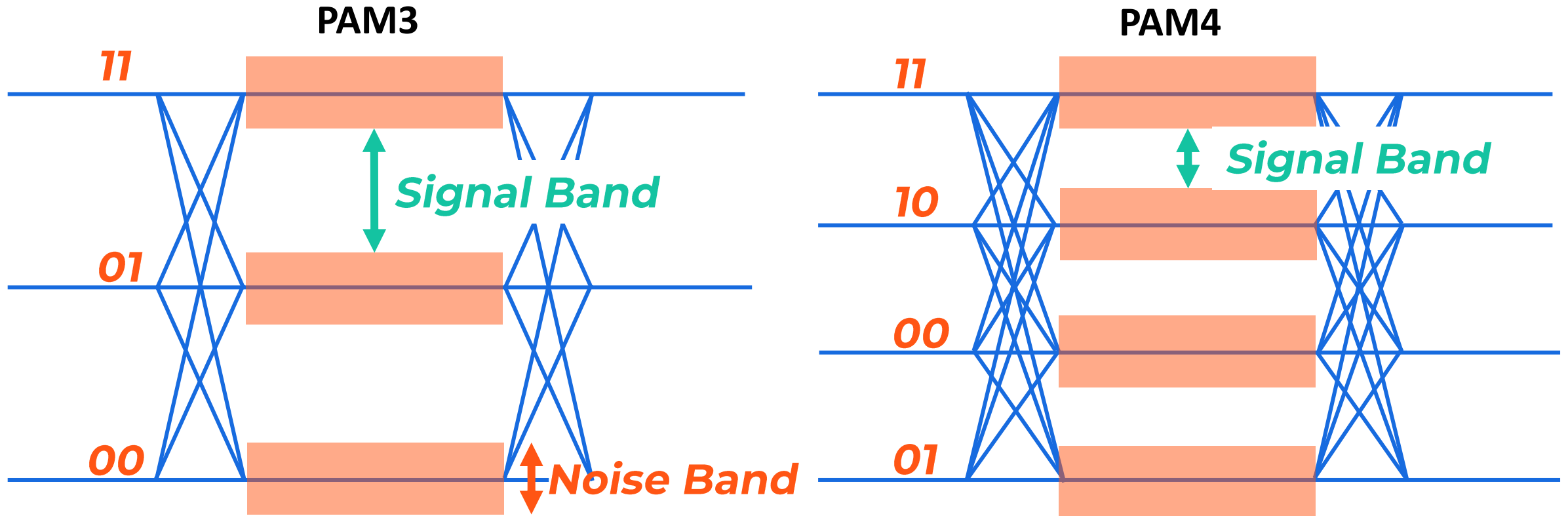


# Backup



# Why PAM3 and not PAM4?

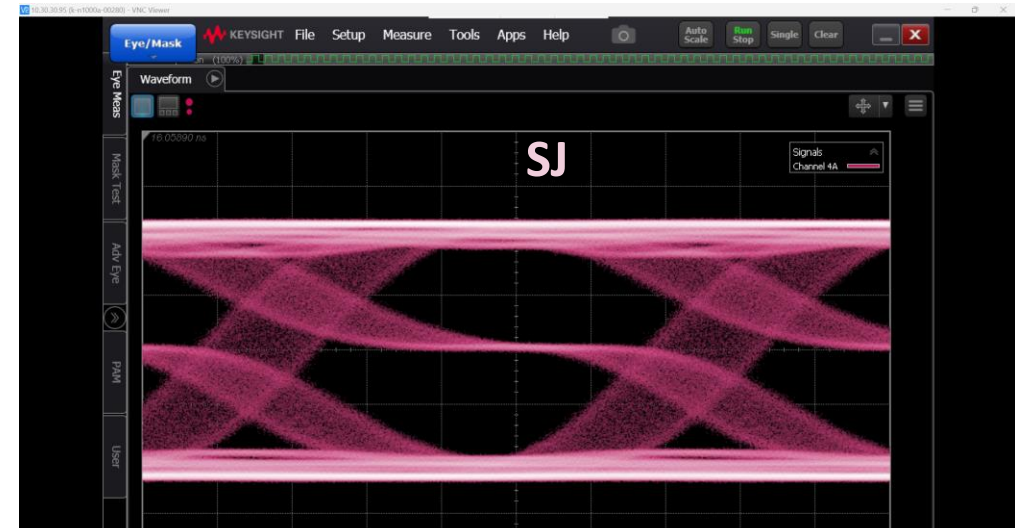
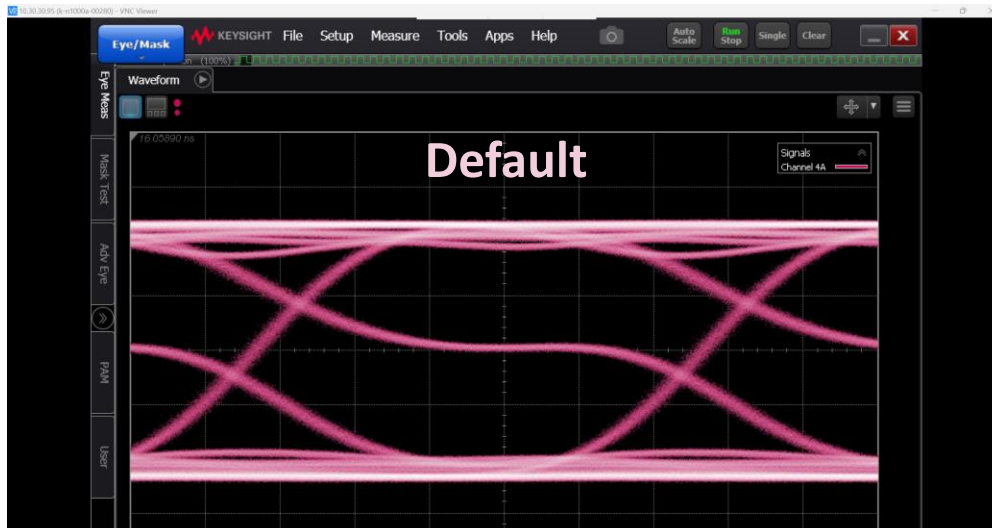
Signal to noise ratio (SNR) is much better in PAM3



For the same noise level, the PAM3 signal eye is much larger



# Stressed-Eye Generation With Simple Pattern



# Progressively Degraded PAM3 Waveforms



# Agenda

- Overview of GDDR7
- Goals of the ATE on Bench Design
- Pin Electronic Design
- Transmitter Characterization
- Receiver Characterization
- Memory functional stress testing

